

Electrically Pumped VECSELs and MIXSELs

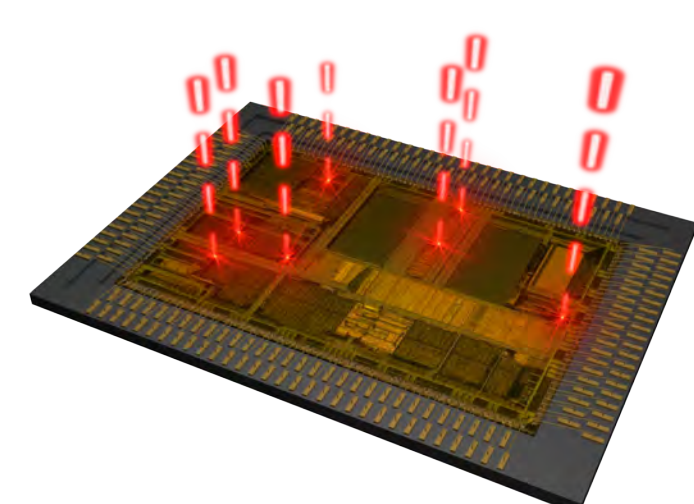
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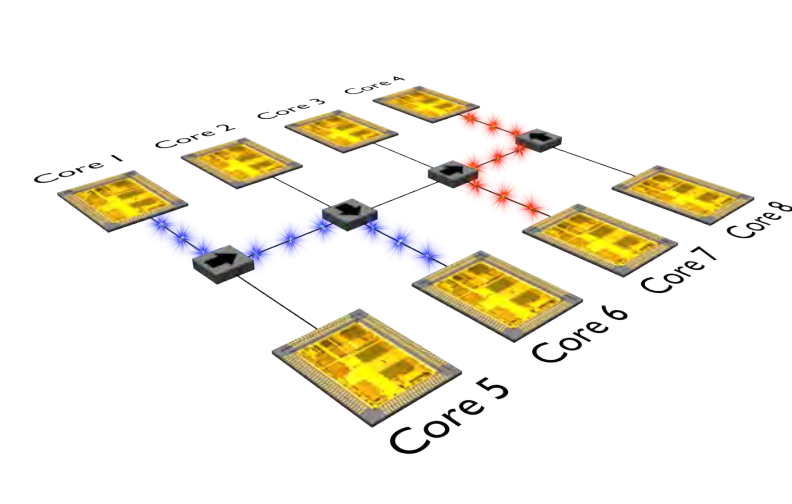
²Philips Technologie GmbH Photonics Aachen, Steinbachstrasse 15, 52074 Aachen, Germany

³Philips Technologie GmbH U-L-M Photonics, Lise-Meitner-Strasse 13, 89081 Ulm, Germany

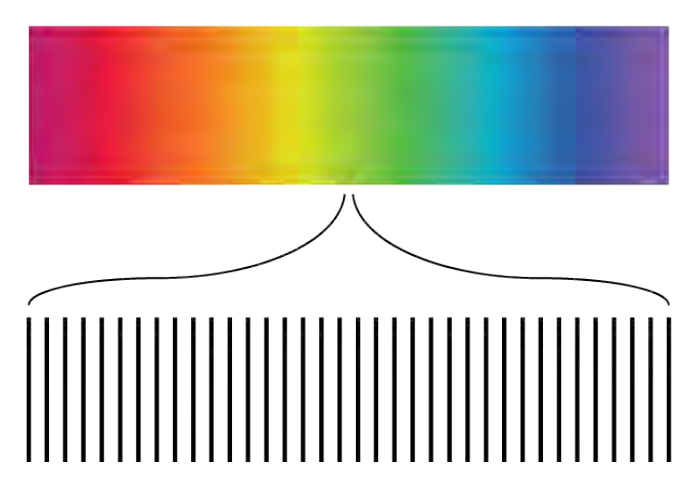
Ultrafast semiconductor lasers



multi-core clocking



optical interconnects



GHz frequency combs

SESAM-modelocked VECSELs ideally suited for pulse generation in GHz regime

Recent achievements from VECSELs:

- 3.3 W in 400 fs pulses [1]
- first f_{CEO} detection from a VECSEL [2]

[1] K. G. Wilcox et. al., Opt. Exp. 21 (2), 1599-1605, 2013.

[2] C. A. Zaugg et. al., submitted to 6th EPSQED Europhoton Conference, 2014

Recent achievements from MIXSELs:

- high-power femtosecond pulses [3]
- 5 to 100 GHz repetition rate [4]

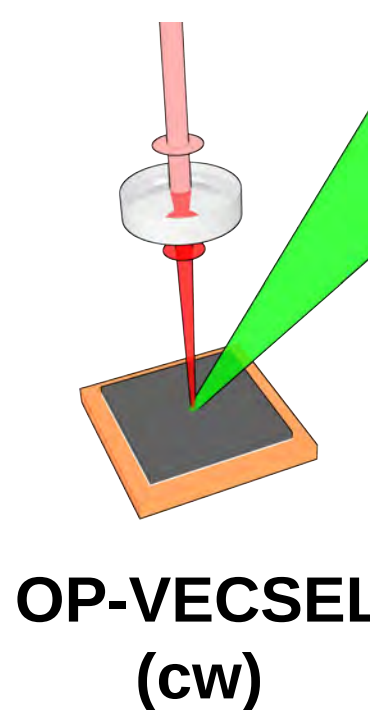
[3] M. Mangold et. al., Opt. Exp. vol. 21 (21), 24904-24911, 2013

[4] M. Mangold et. al., Opt. Exp. vol. 22 (5), 6099-6107, 2014

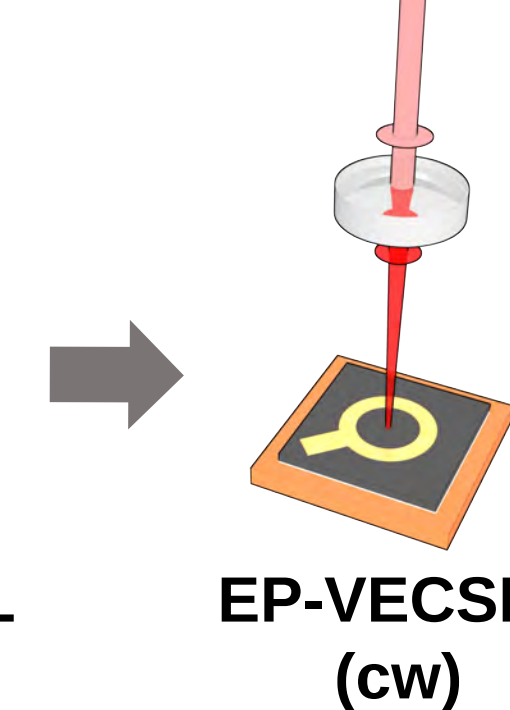
Electrically Pumped VECSELs

Why electrical pumping?

- much more compact (no pump!)
- mass producible
- inexpensive fabrication
- keep advantages (e.g. beam quality, power scaling, suitable for modelocking)



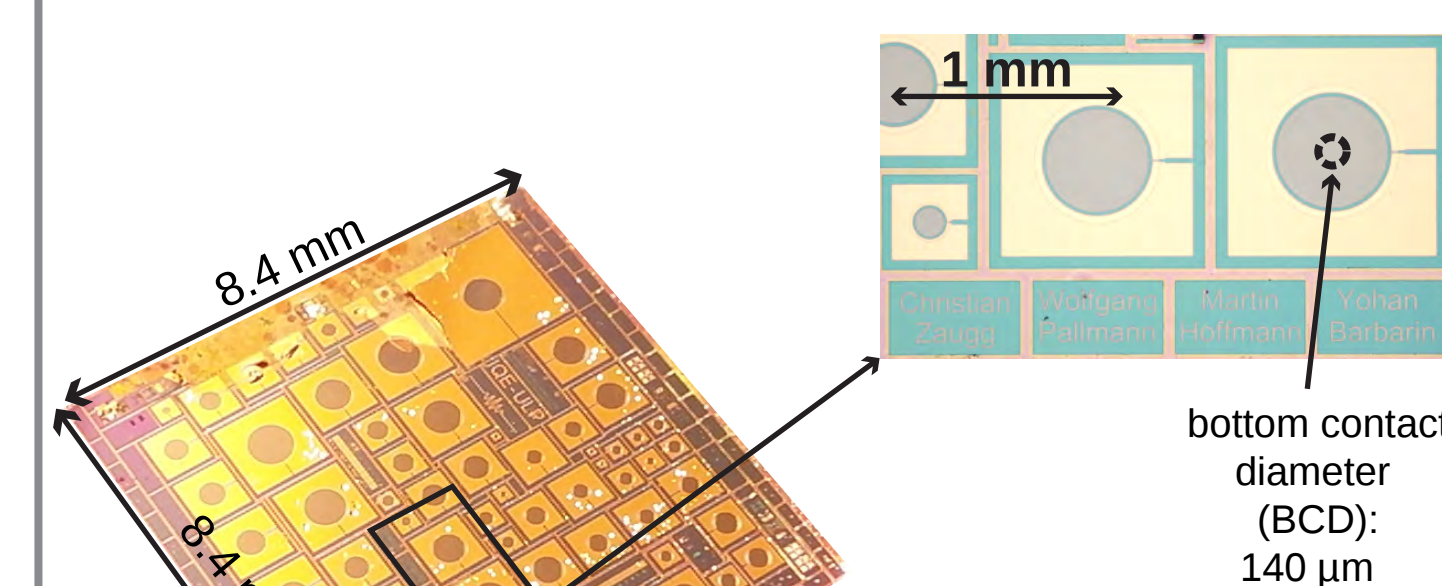
OP-VECSEL (cw)



EP-VECSEL (cw)

Recent results:

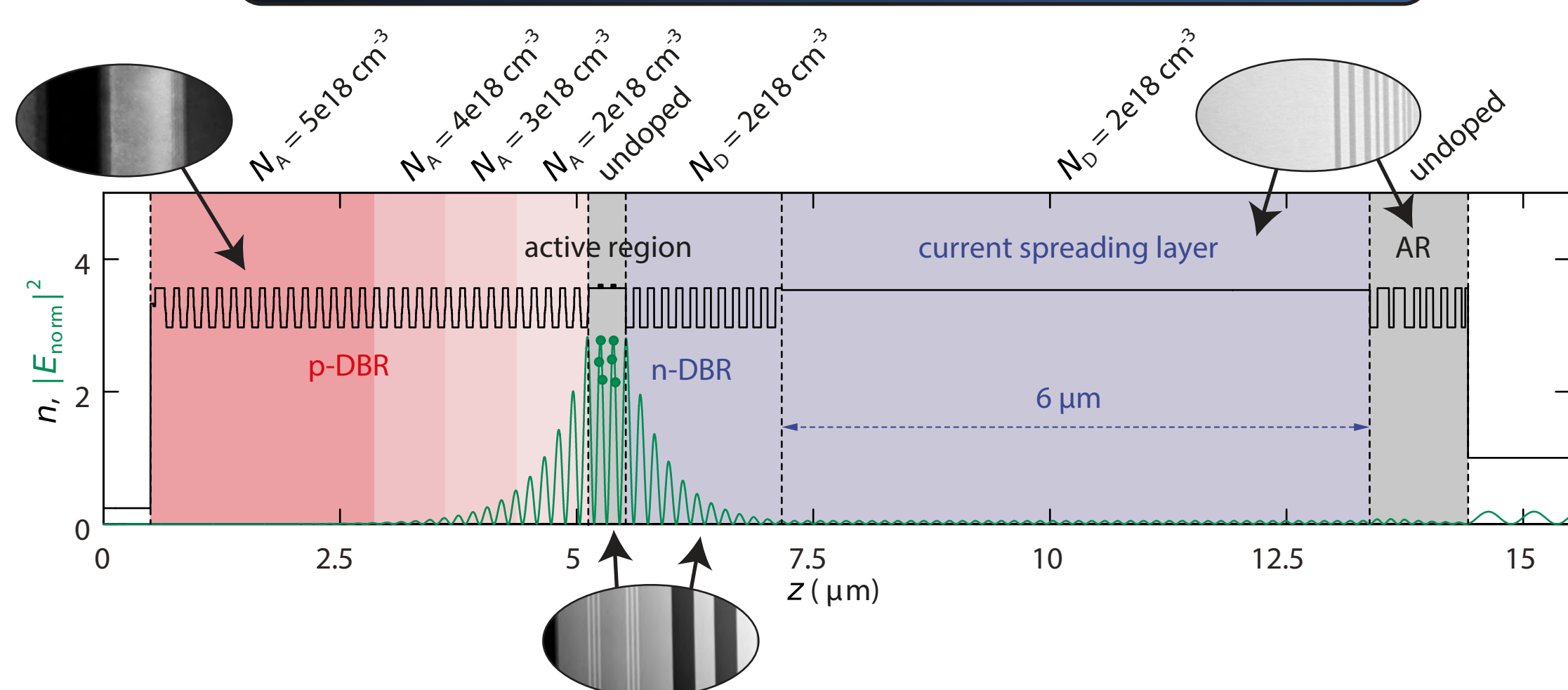
13.1 mW with 7.3 ps pulses [5]



[5] W. P. Pallmann, C. A. Zaugg, M. Mangold, I. Dahhan, M. Golling, B. W. Tilma, B. Witzigmann, U. Keller, "Ultrafast electrically pumped VECSELs" IEEE Photonics Journal, vol. 5, Nr. 4, 1501207, 2013

VECSEL gain chip, SESAM and cavity setup

Principle of EP-VECSEL gain chip



refractive index profile, normalized electrical field distribution and doping profile of the initial EP VECSEL gain structure with TEM insets [5]

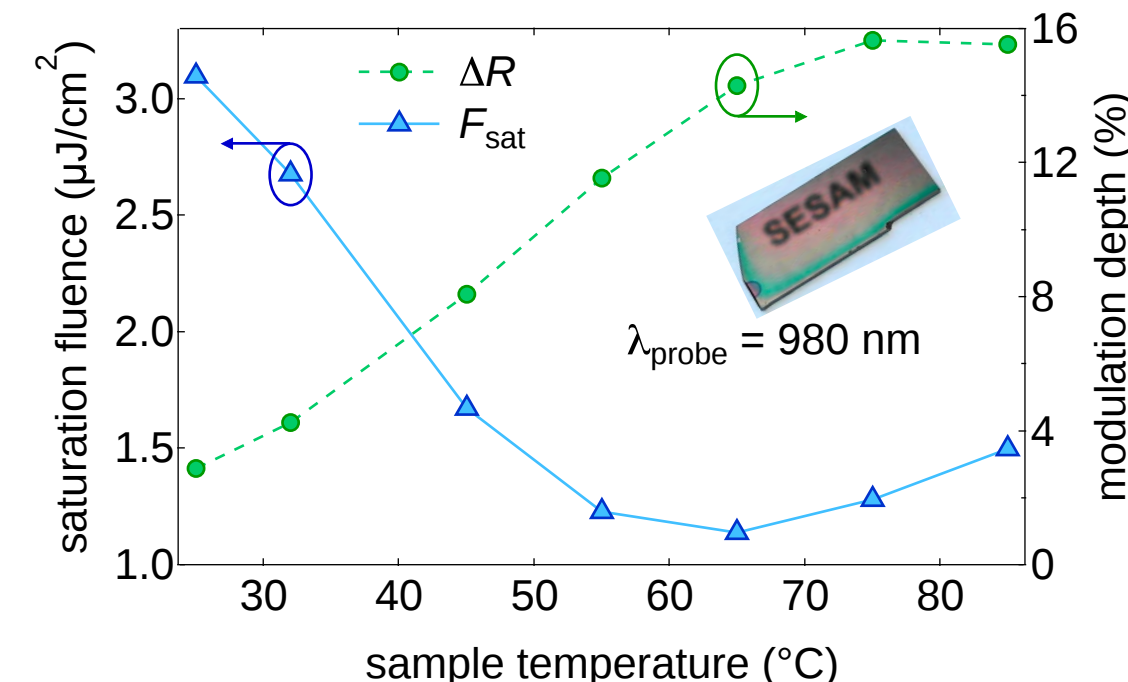
EMEZ
Electron Microscopy ETH Zurich

Improved SESAM

requirements for EP-VECSEL modelocking

low saturation fluence high modulation depth fast recovery time

low-temperature, AIAs embedded QW-SESAM highly resonant dielectric top-coating: [6]



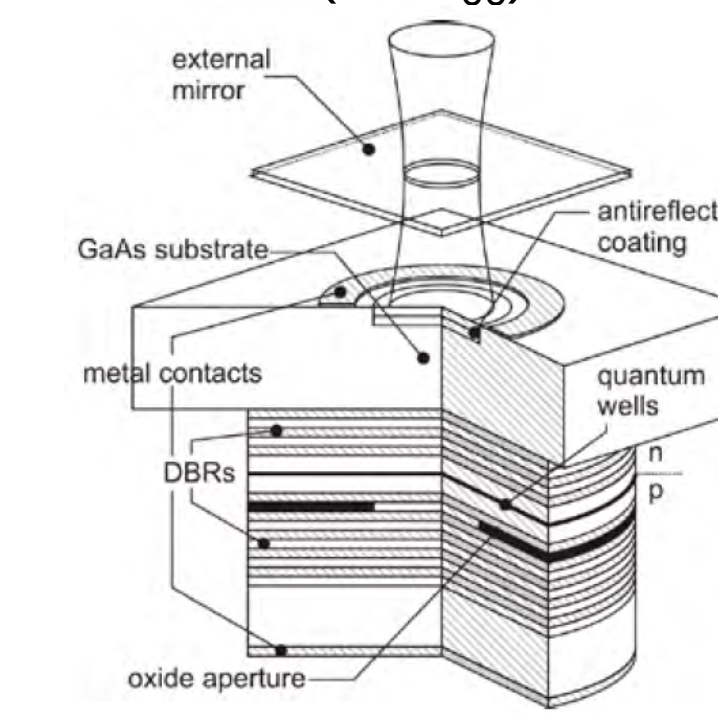
[6] C. A. Zaugg, S. Gronenborn, H. Moench, M. Mangold, M. Miller, U. Weichmann, W. P. Pallmann, M. Golling, B. W. Tilma, U. Keller, Appl. Phys. Lett., vol. 104, 121115, 2014

[7] H. Moench, A. Andreadaki, S. Gronenborn, J. S. Kolb, P. Loosen, M. Miller, T. Schwarz, A. M. Van Der Lee and U. Weichmann, at SPIE Photonics West, San Francisco, 2014.

Improved gain chips

optimized gain chip from Philips [7]

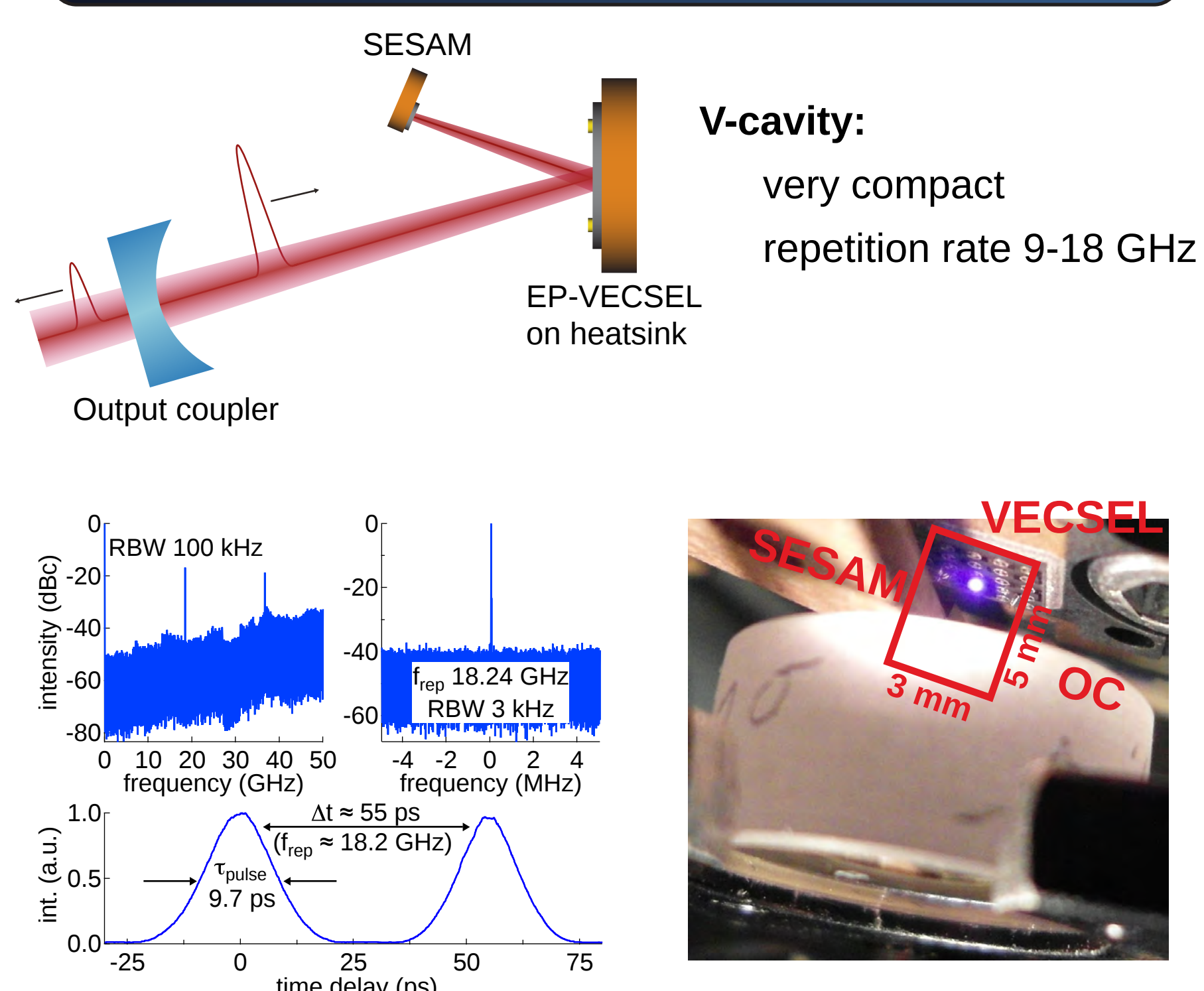
high power high beam quality (TEM₀₀) low resonance in active region



average power >100 mW single mode Suitable for SESAM modelocking

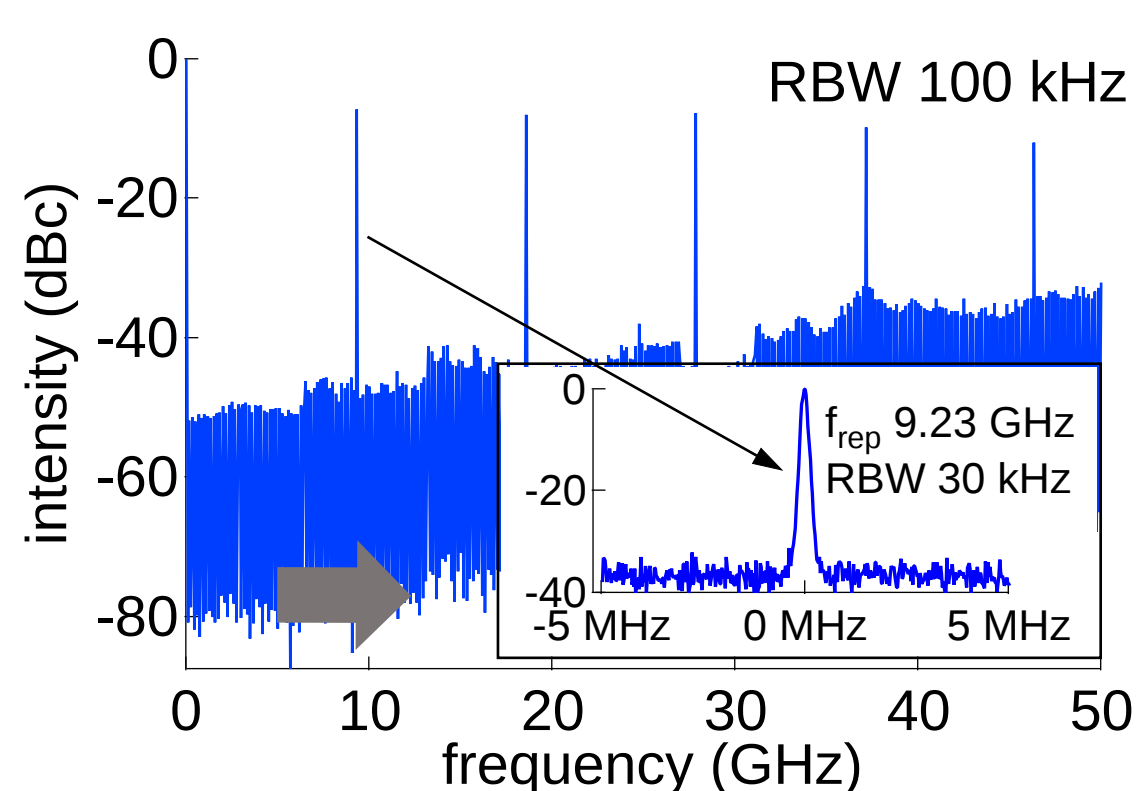
Experimental results:

Highest repetition rate



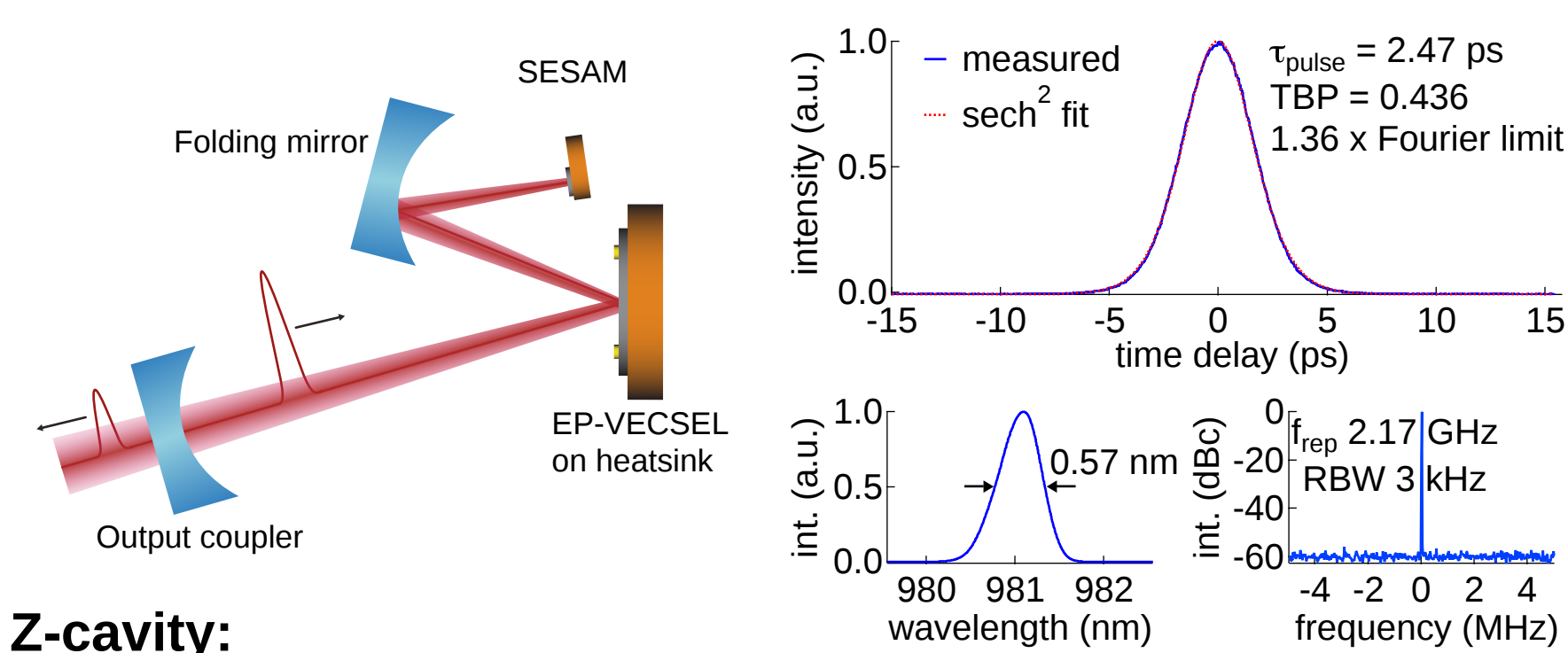
repetition rate: >18 GHz! *2

Highest average power



average power: >50 mW! *1

Shortest pulses



pulse duration: 2.5 ps! *3

Summary of new results

	P_{avg} [mW]	f_{rep} [GHz]	T_{pulse} [ps]	P_{peak} [W]
*3	53.2	9.2	2.91	1.74
*2	10.1	18.2	9.48	0.05
*1	15.9	2.2	2.46	2.62
	35.0	2.2	3.03	4.73

Record performance from modelocked EP-VECSEL:

Highest average power
Highest repetition rate
Shortest pulses
Highest peak power

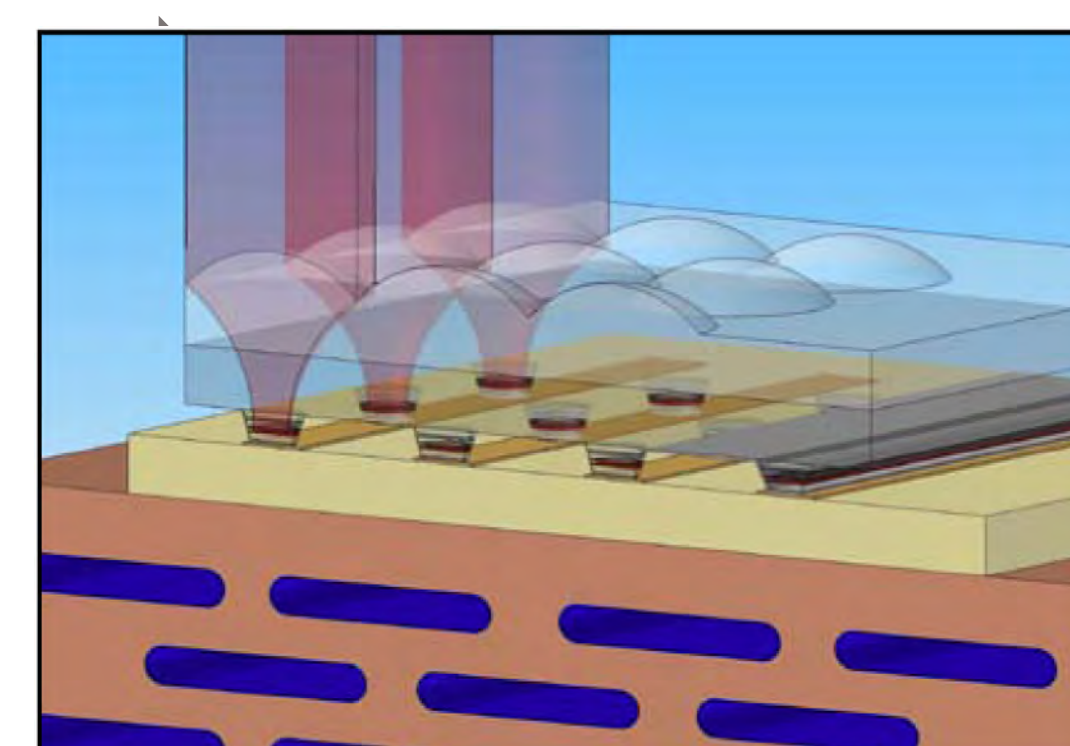
Outlook

near future:

further increase power towards 500 mW
decrease pulse duration by less resonant chips

goal: EP MIXSEL

integration of SESAM into EP VECSEL



ultracompact device with:
- GHz repetition rate
- high power
- excellent beam quality

wafer-scale integration scheme possible!

our work is supported by:

